

High-efficiency photovoltaics based on semiconductor nanostructures

Program Team: PV

Edward T. Yu

University of Texas at Austin/University of California at San Diego

ety@ece.utexas.edu

26 May 2010

Timeline

- Start date: 1 February 2008
- End date: 31 January 2011
- Percent complete: 70%

Budget

- Total project funding
 - DOE share: \$604,000
 - Contractor share: 20% cost sharing
- Funding received in FY09: \$224,000
- Funding for FY10: \$140,000 to date

Barriers

- Very high-efficiency solar cells an essential component for concentrating PV
- Robustness under spectral variability desirable
 - ⇒ single pn junction structures
 - ⇒ multijunction, non-series connected devices

Partners

- Project lead:
 - University of California, San Diego
 - University of Texas at Austin
- Interactions/collaborations:
 - Spire Semiconductor
 - Jet Propulsion Laboratory
 - Boeing/Spectrolab

Challenges

- High-efficiency solar cells required for applications such as terrestrial concentrating photovoltaics
- Quantum-well solar cells and related structures offer potential for very high efficiency (~45% to >60% theoretically predicted efficiencies)
- Substantial challenges in materials and devices:
 - High quality heterostructures to minimize recombination rates
 - Engineering carrier and photon transport paths to achieve simultaneously high efficiency in photon absorption and photogenerated carrier collection

Importance

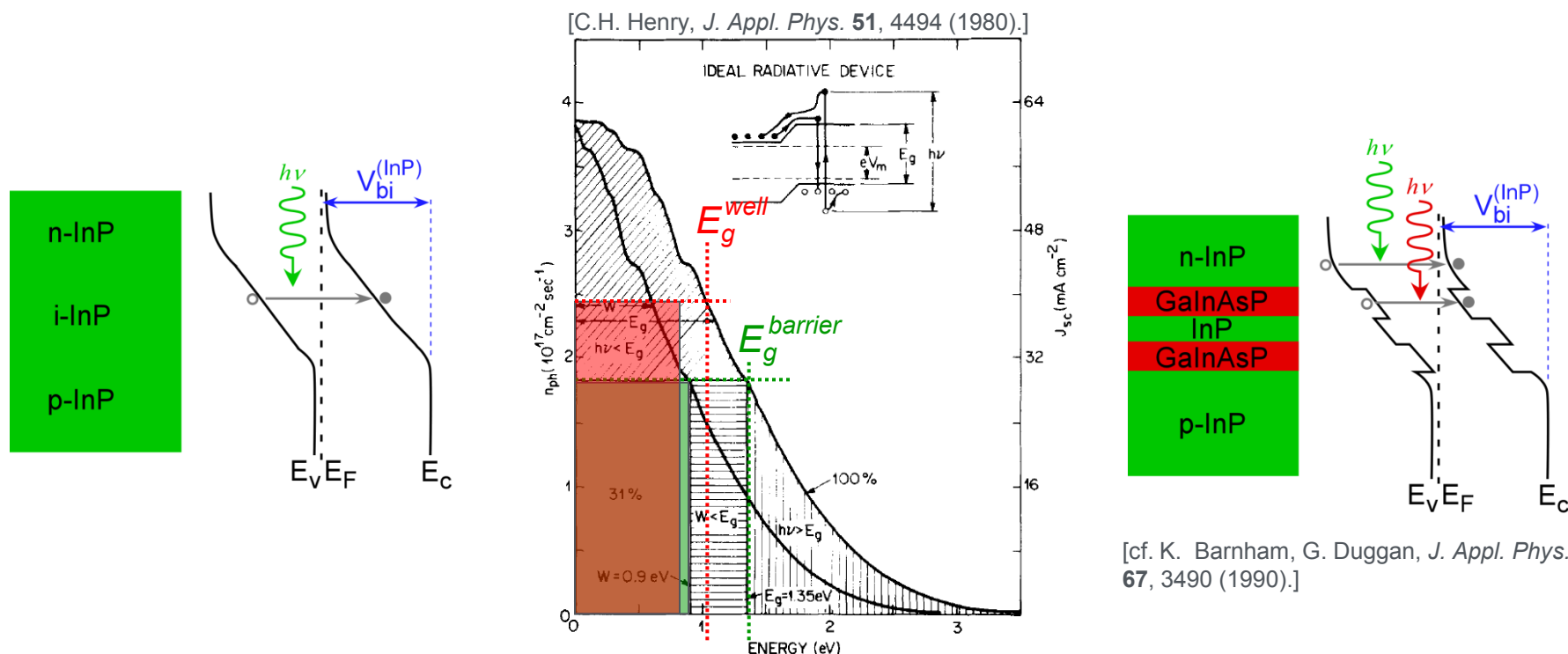
- Multijunction tandem solar cells can provide high efficiency, but potentially sensitive to terrestrial spectral variations
- Single pn junction structures (e.g., quantum-well, intermediate-band solar cells, etc.) can theoretically provide comparable efficiency with much less spectrum sensitivity
- Success in developing high-efficiency devices of these types should improve viability of large-scale concentrating photovoltaic systems

Objectives

- Overall objective: development and demonstration of high-efficiency photovoltaic device concepts based on semiconductor nanostructures
 - Quantum-well solar cells and related devices
 - Nanowire-based solar cells
- 2009-2010 objective: build upon initial demonstrations of key device concepts to explore routes to increased power conversion efficiency
 - Engineering of waveguiding properties of quantum-well solar cell devices for photon management
 - Optimization of internal quantum-well structure for increased optical absorption
 - Improved growth and fabrication of nanowire-based solar cell structures

Relevance

- 2009-10 objectives represent key steps in realization of devices with high absolute levels of power conversion efficiency
- High absolute power conversion efficiency in quantum-well solar cells or other single-pn junction photovoltaic devices will enable high efficiency to be achieved over broad range of illumination spectra
- Devices developed in this project could be a key component in terrestrial concentrating photovoltaic systems



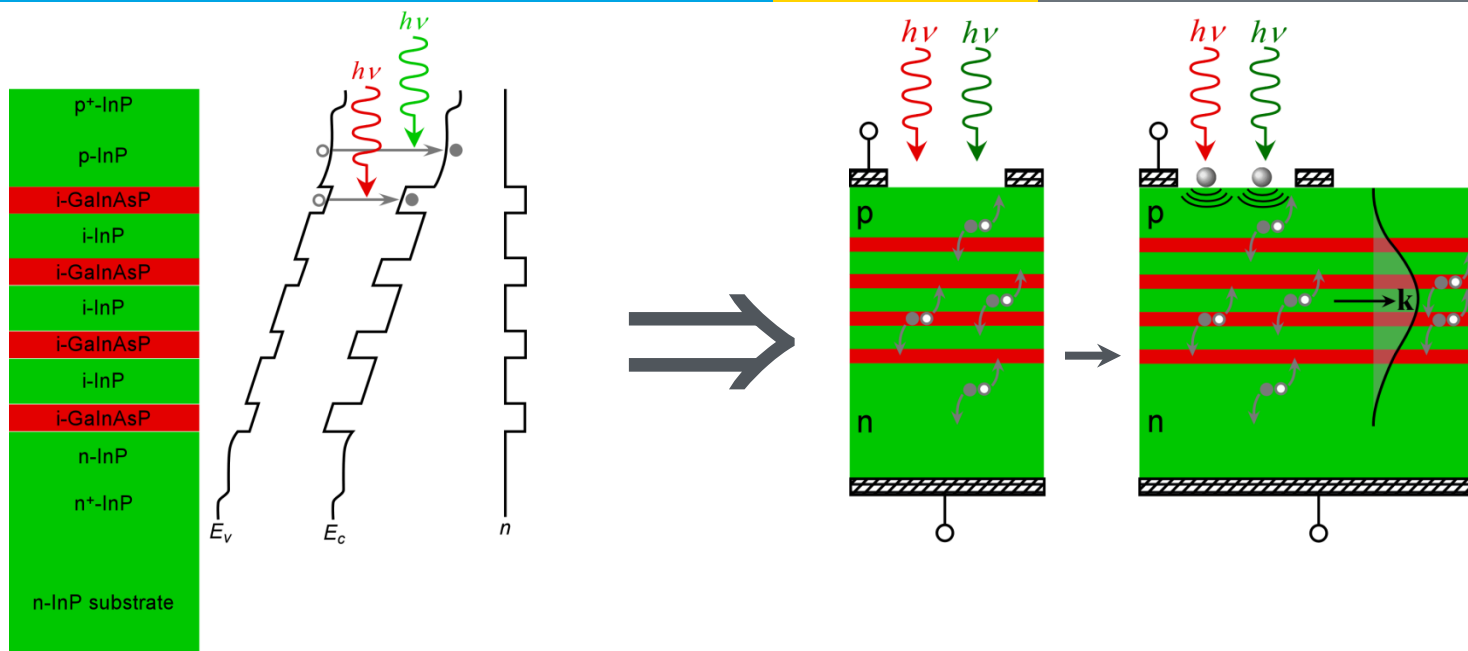
Predicted maximum power conversion efficiencies for quantum-well solar cells are ~45% to ~63% (vs. ~31% to ~37% for “conventional” solar cell)

[G. Wei, K.T. Shiu, N.C. Giebink, S.R. Forrest, *Appl. Phys. Lett.* **91**, 223507 (2007);
S.P. Bremner, R. Corkish, C.B. Honsberg, *IEEE Trans. Electron Devices* **46**, 1932 (1999).]

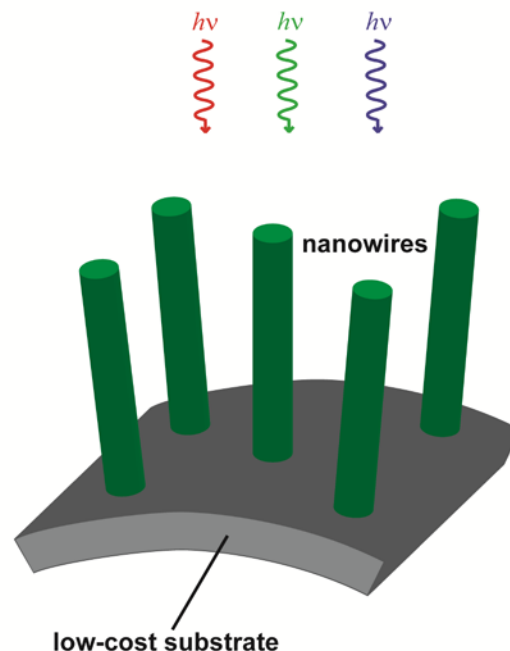
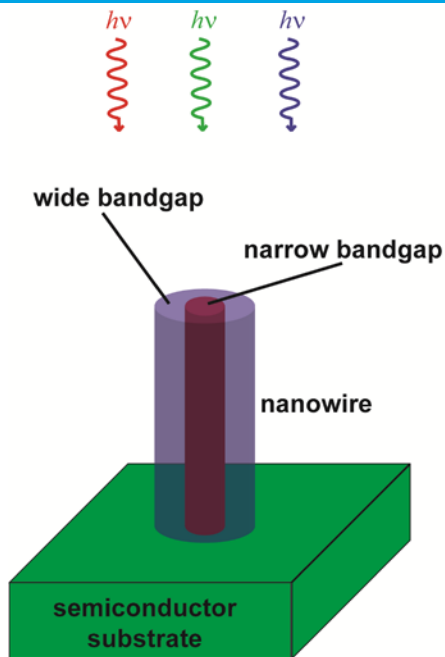
Quantum well solar cell challenges

- Multiple-quantum-well materials issues, e.g., critical thickness, interface quality, recombination
- High quantum efficiency in long-wavelength absorption
- Efficient carrier extraction from quantum wells

Approach – quantum-well solar cells and photon management



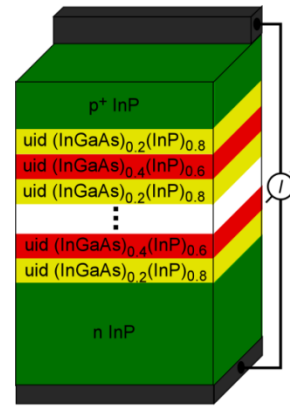
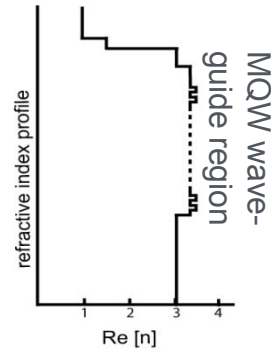
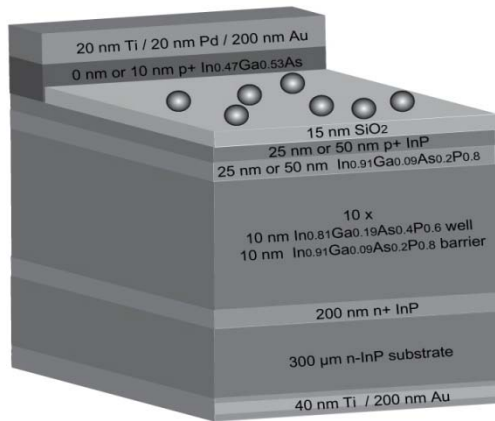
- In conventional device geometry, design requirements for efficient photon absorption and efficient photogenerated carrier collection are incompatible
 - Efficient absorption requires thickness $\sim 1\mu\text{m}$
 - Efficient carrier collection requires thickness $\sim 0.2\text{--}0.3\mu\text{m}$
- Index contrast leads to optical confinement in multiple-quantum-well region
 - \Rightarrow optically confined, lateral photon propagation paths supported
- Metal (or dielectric) nanoparticles can scatter photons into lateral paths
 - Broader-band effect than, e.g., grating scatterers
 - Easy to fabricate



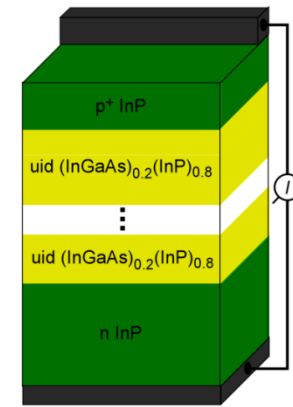
- Core-shell nanowires can enable realization of quantum-well solar cell concept in alternate geometry with potentially relaxed lattice mismatch constraints
- Nanowire-based photovoltaics could facilitate use of high-quality, crystalline semiconductor material with support substrates that are low-cost, flexible, etc.

- Key project collaborators
 - Spire Semiconductor: collaboration in development and supply of epitaxial heterostructure material for quantum-well solar cells and related structures.
 - NASA Jet Propulsion Laboratory: collaboration in development and implementation of wafer thinning and substrate removal processes.
 - Boeing/Spectrolab: collaboration in adaptation of nanoparticle scattering effects for multijunction tandem solar cells.
 - University of Karlsruhe: collaboration in development of quantum dot and dot-in-well structures for high-efficiency solar cells.
- Collaborators listed here are not funded through this DOE program.

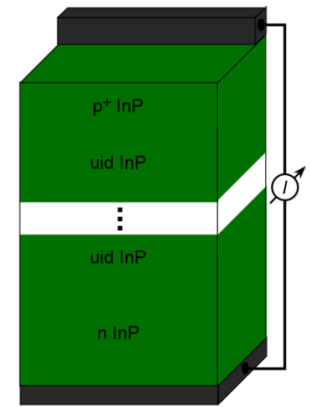
Results – QWSC demonstration



Quantum-well device

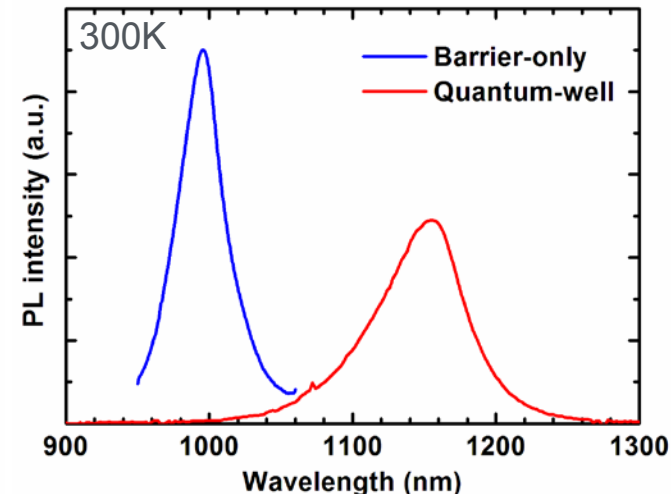
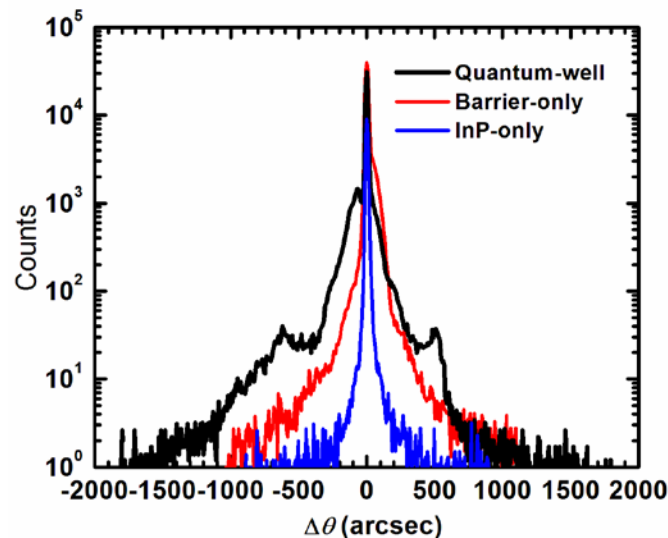


Barrier-only control device

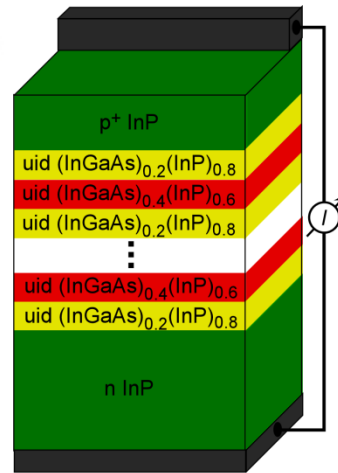
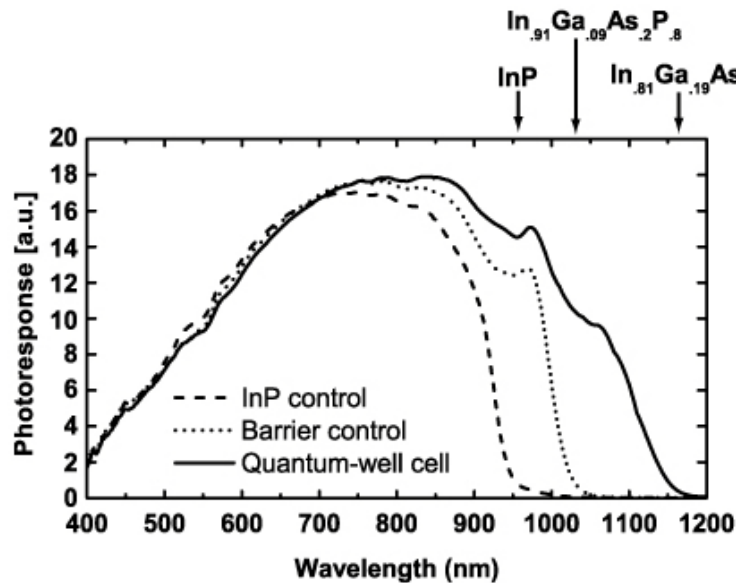


InP-only control device

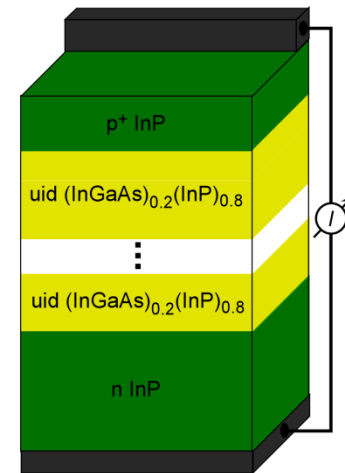
- MQW absorption and nanoparticle scattering concepts demonstrated in lattice-matched InP/InGaAsP MQW structures grown by MOCVD
- Room-temperature photoluminescence and x-ray diffraction confirm reasonable lattice match, reduced band gap in quantum-well layers



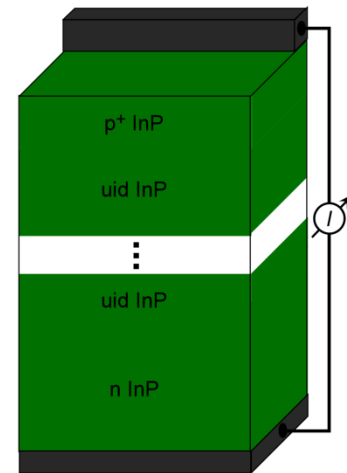
Results – QWSC demonstration



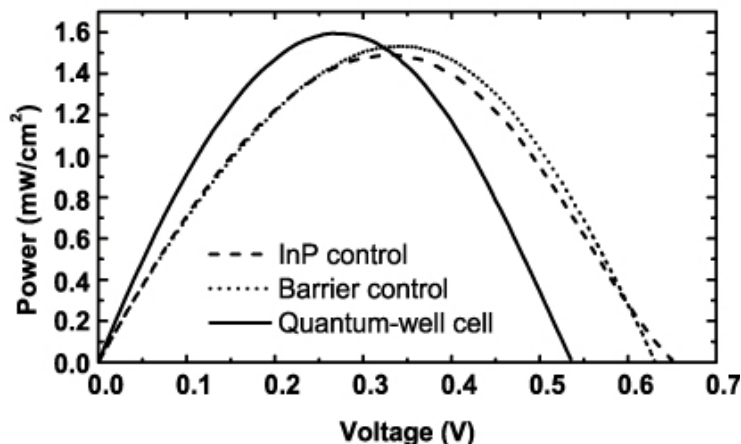
Quantum-well device



Barrier-only control device

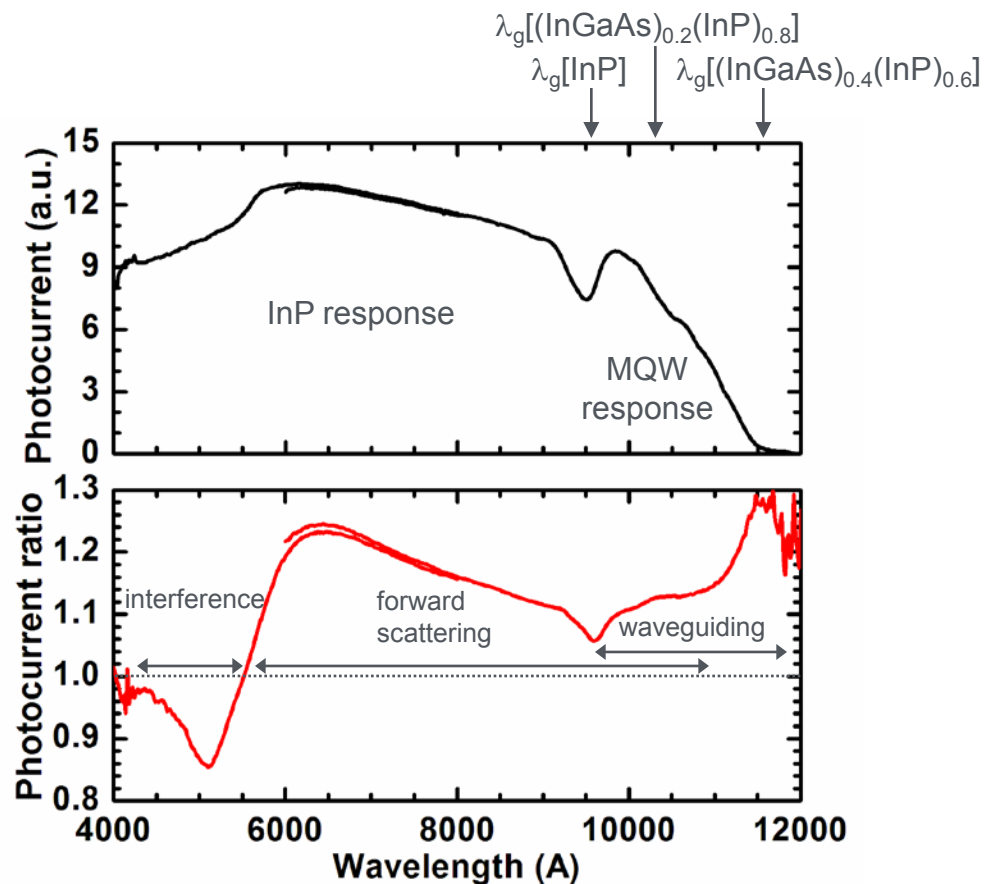
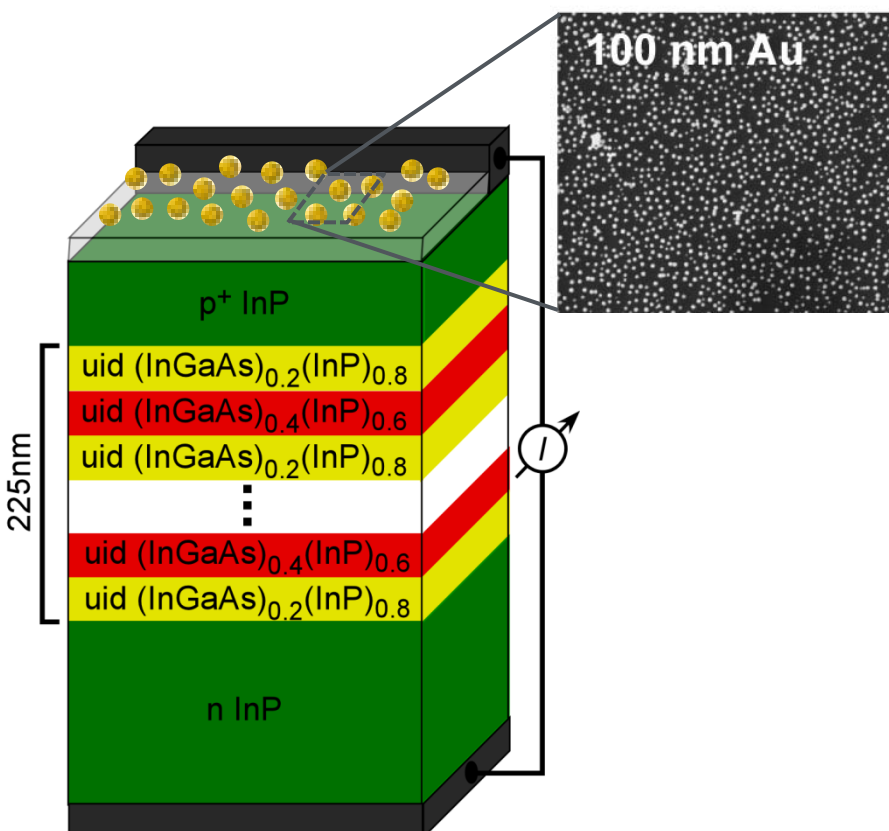


InP-only control device



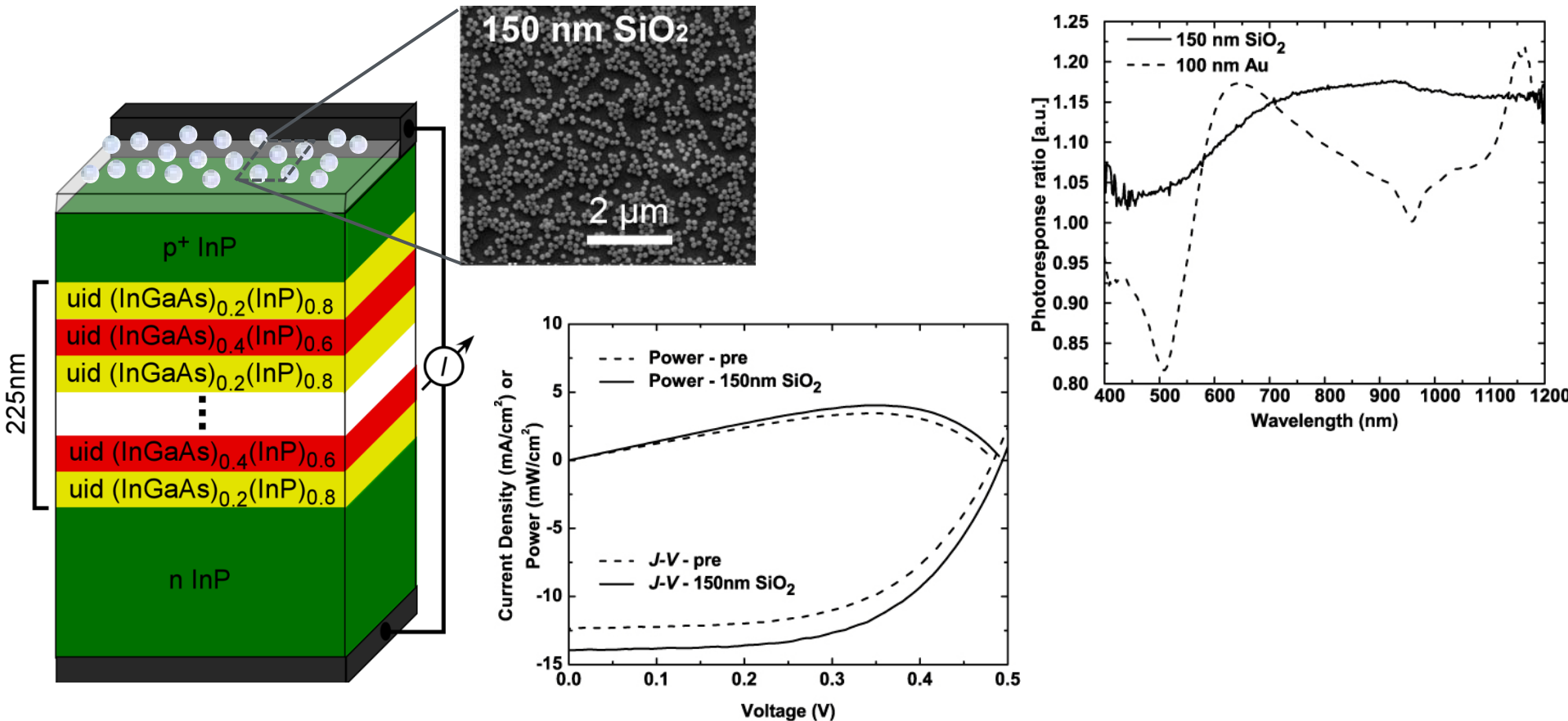
- Barrier-only and quantum-well devices show clear photocurrent response at wavelengths beyond InP band gap
- Quantum-well device shows ~5-7% increased power output over barrier-only and InP-only control devices

Results – QWSC demonstration

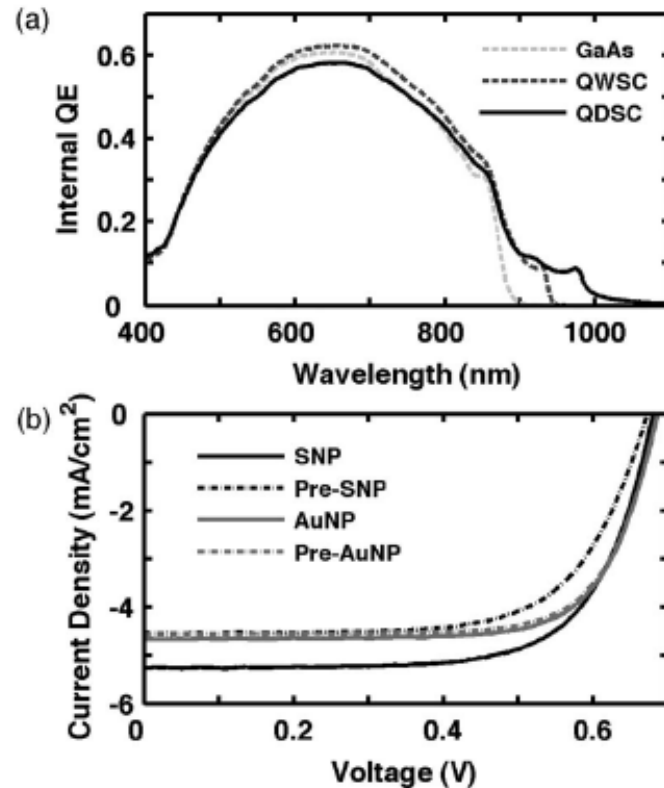
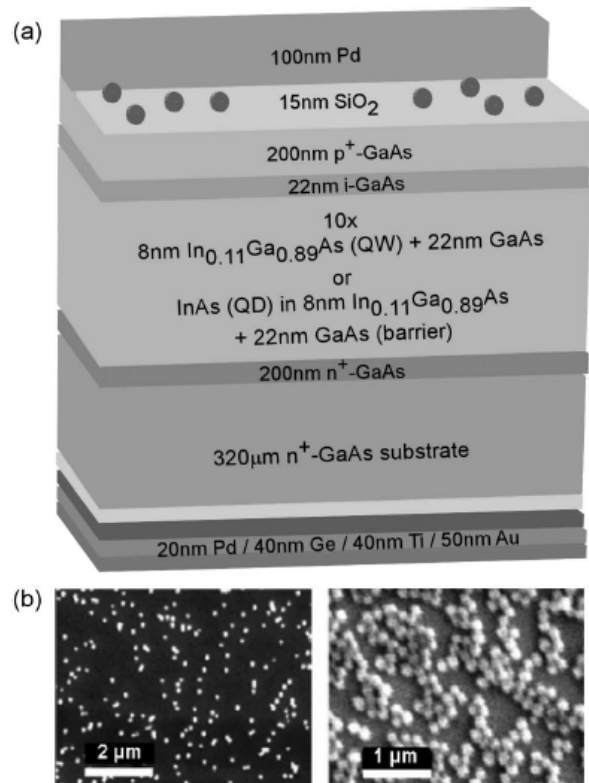


- InGaAsP-InP multiple-quantum-well solar cell exhibits clear response below InP bandgap due to MQW absorption
- Functionalization with 100nm Au nanoparticles generates plasmonic effects:
 - Forward scattering into semiconductor device region
 - Excitation of optically confined modes in MQW region

Results – QWSC demonstration

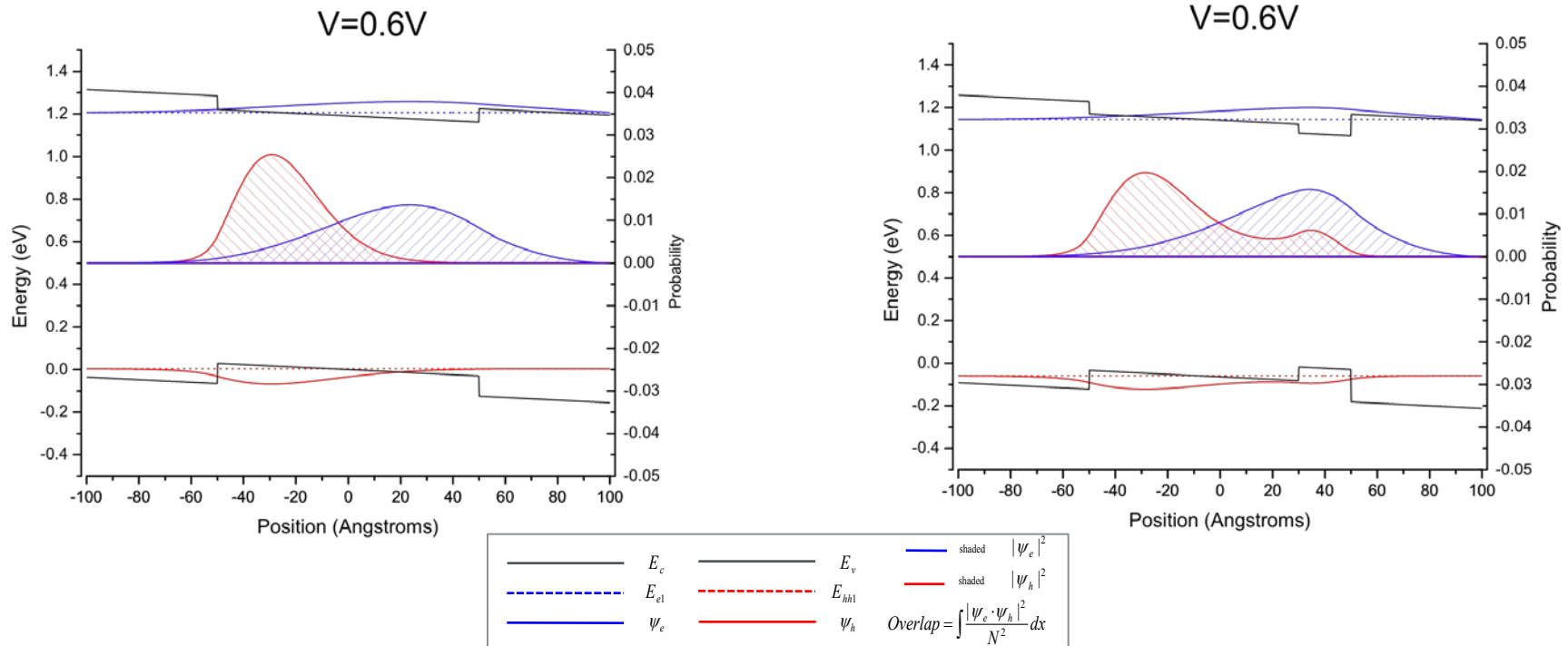


- Highly unoptimized device shows ~13% increase in short-circuit current density, ~17% increase in power conversion efficiency due to SiO₂ nanoparticle scattering
- Au nanoparticles yielded ~7% increase in current, ~1% increase in power conversion efficiency



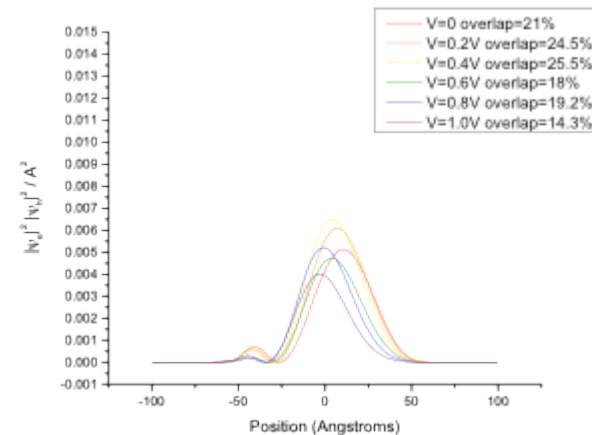
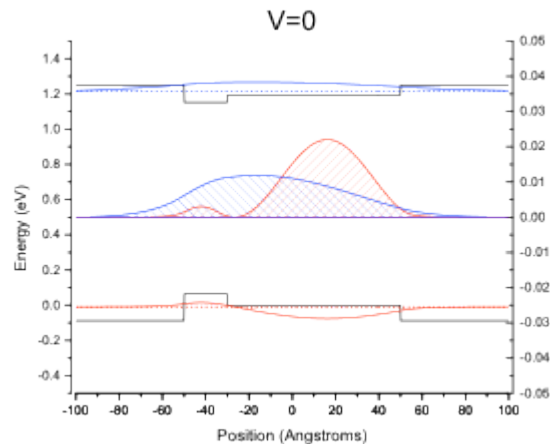
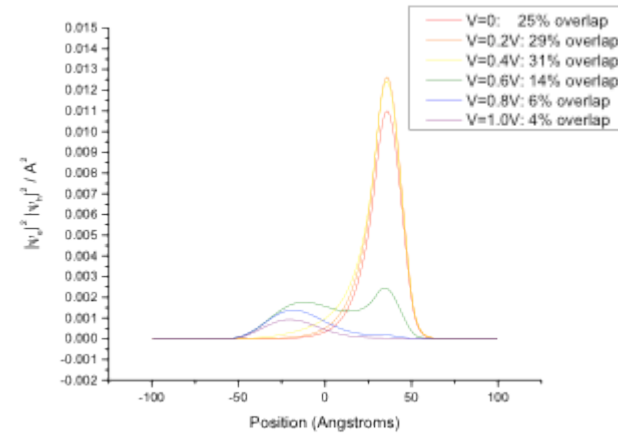
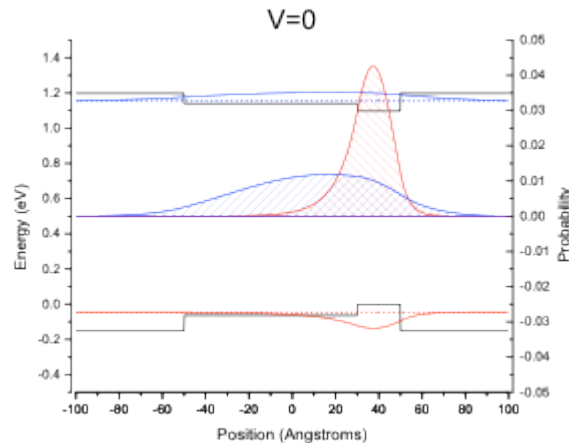
- InAs/InGaAs/GaAs quantum dot-in-well solar cell structures also successfully fabricated and demonstrated
- Quantum-dot structures enable photocurrent response to be extended to longer wavelengths than quantum-well structures
- Nanoparticle scattering effects also enable improved absorption efficiency

Results – engineered quantum-well structures

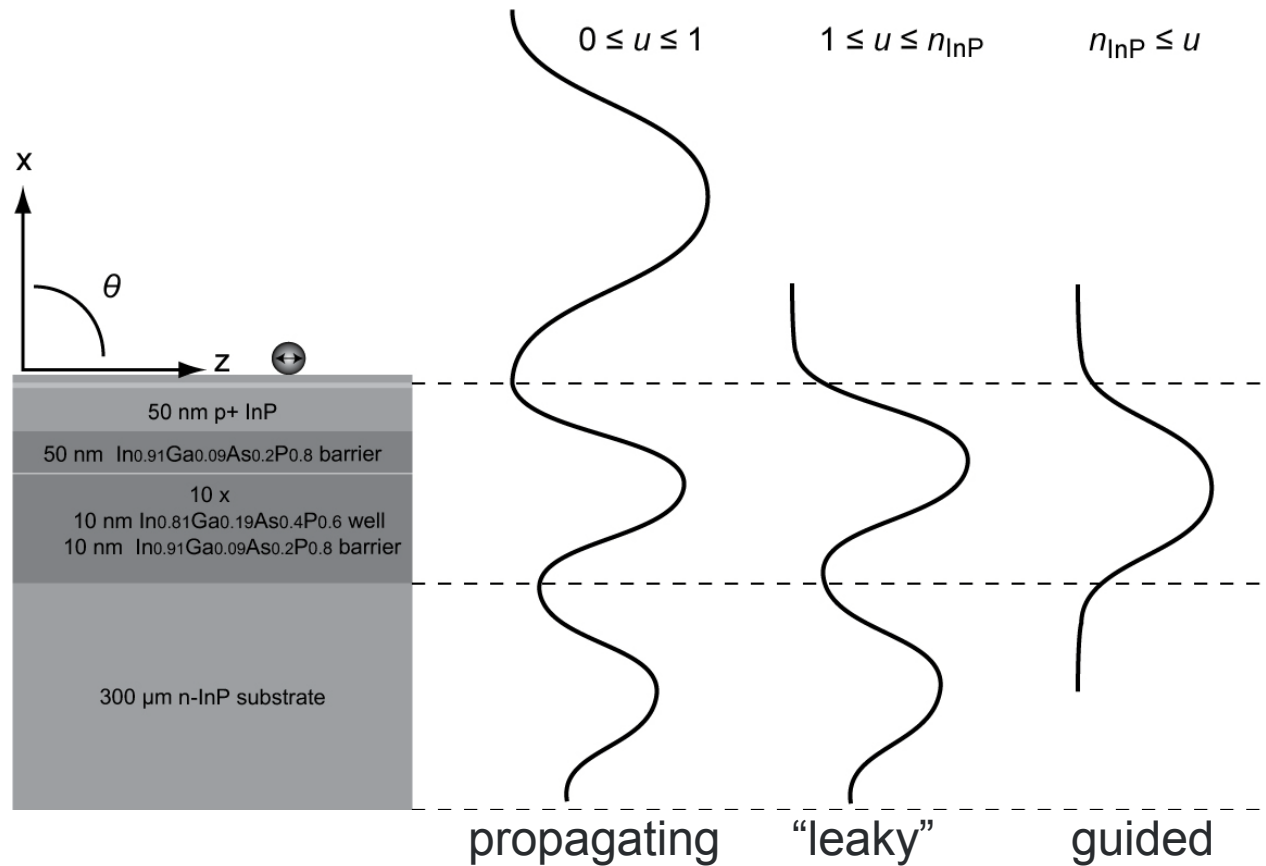


- Introduction of internal structure within quantum well can substantially alter electron-hole wavefunction overlap and optical absorption efficiency
- 1D Poisson-Schrodinger simulations allow internal structure and resulting wavefunctions in quantum wells to be computed and optimized

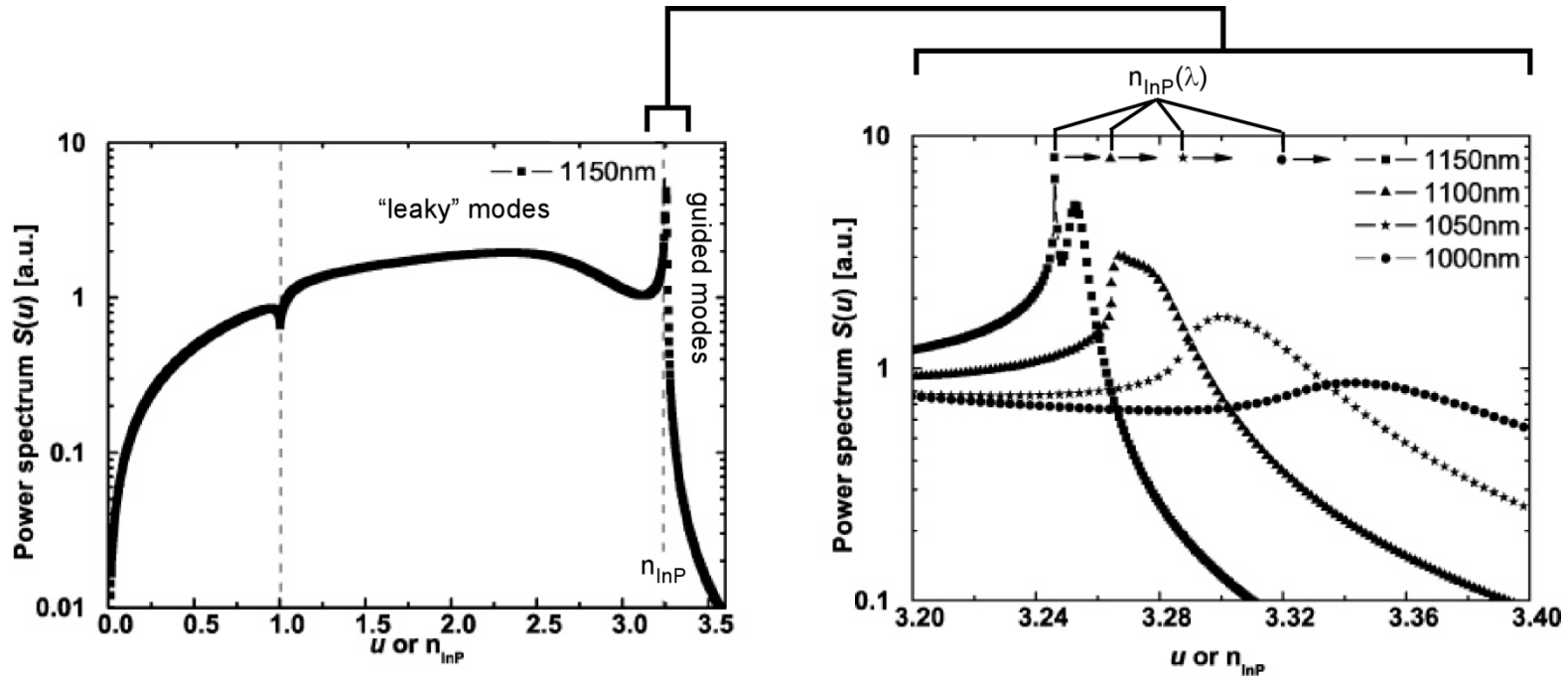
Results – engineered quantum-well structures



- Bias dependence of electron and hole wavefunctions must be taken into account in device designs
- Samples have been grown by MOCVD and experimental measurements are underway

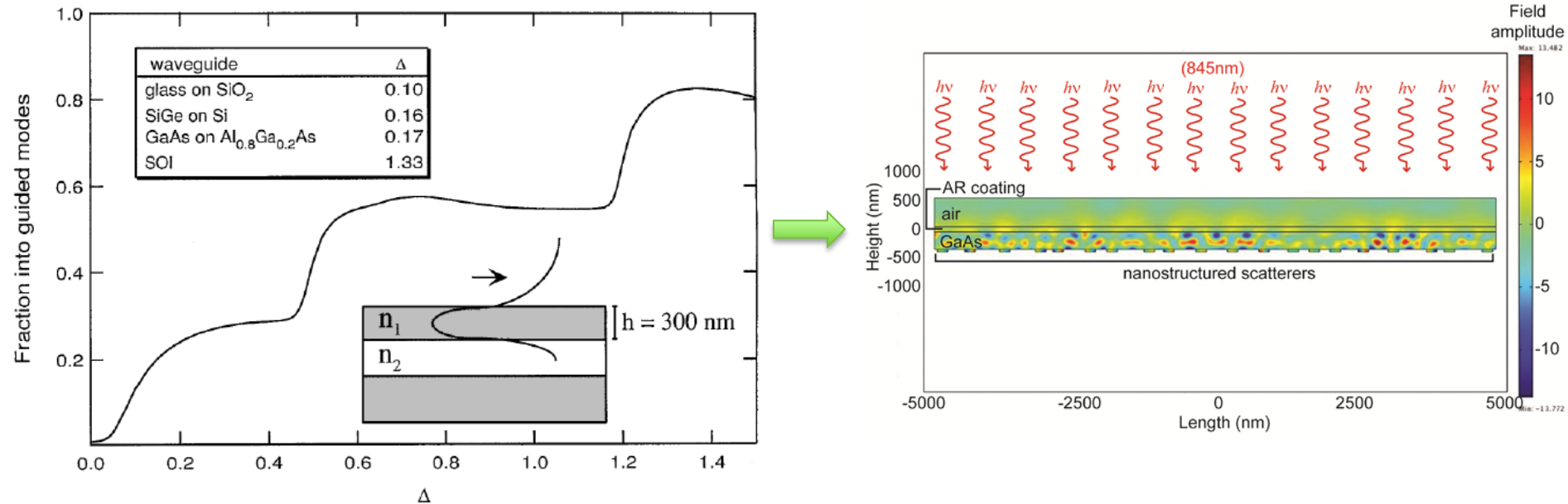


- Coupling of photons scattered by nanoparticles into waveguide modes modeled using horizontal radiating dipole at device surface
- “Leaky” and guided modes could contribute to additional absorption and photocurrent generation in semiconductor



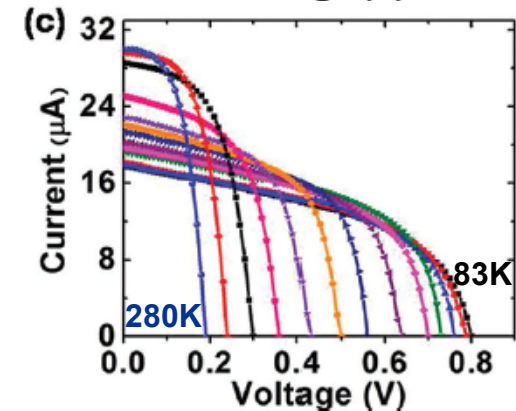
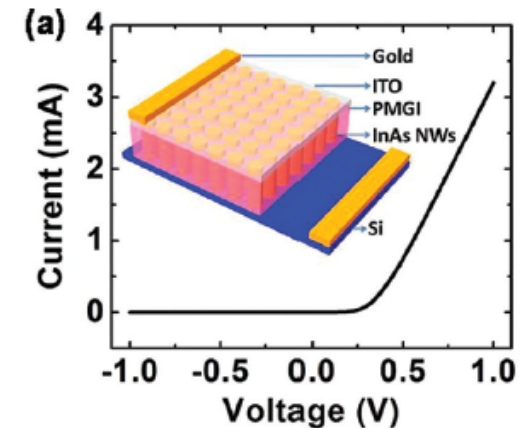
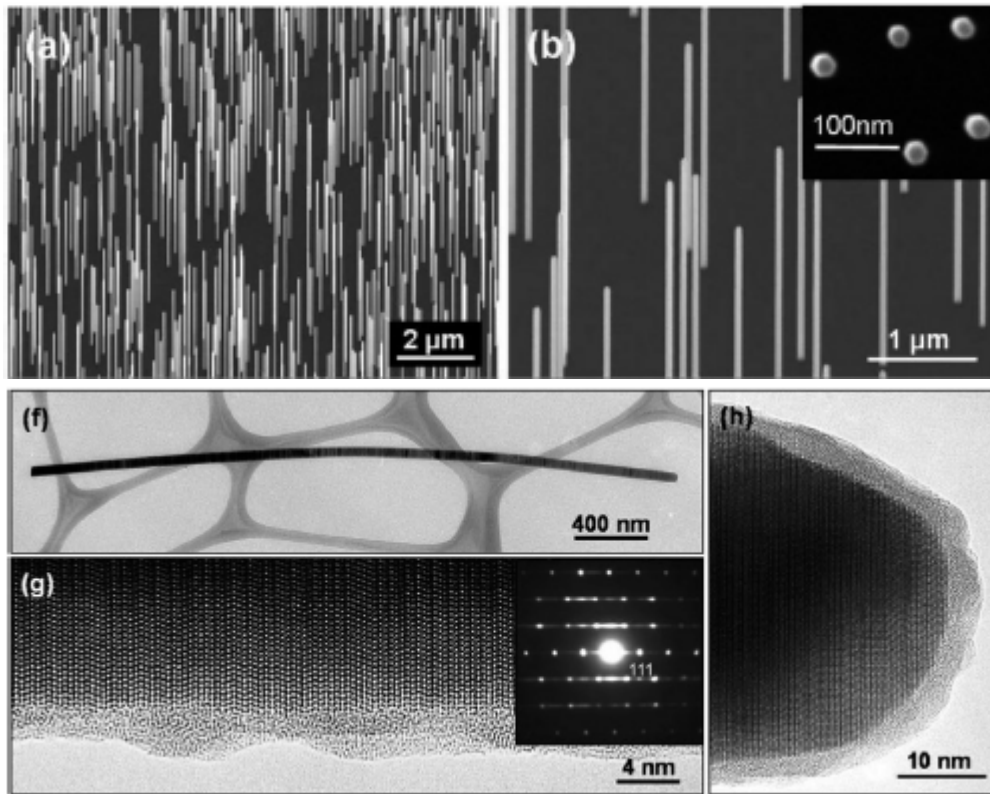
- Coupling efficiency into guided modes $< 10\%$, but coupling into “leaky” + guided modes $\sim 80\text{-}90\%$
- Key issue for efficient coupling into guided modes is large refractive index contrast

Results – optimized device design



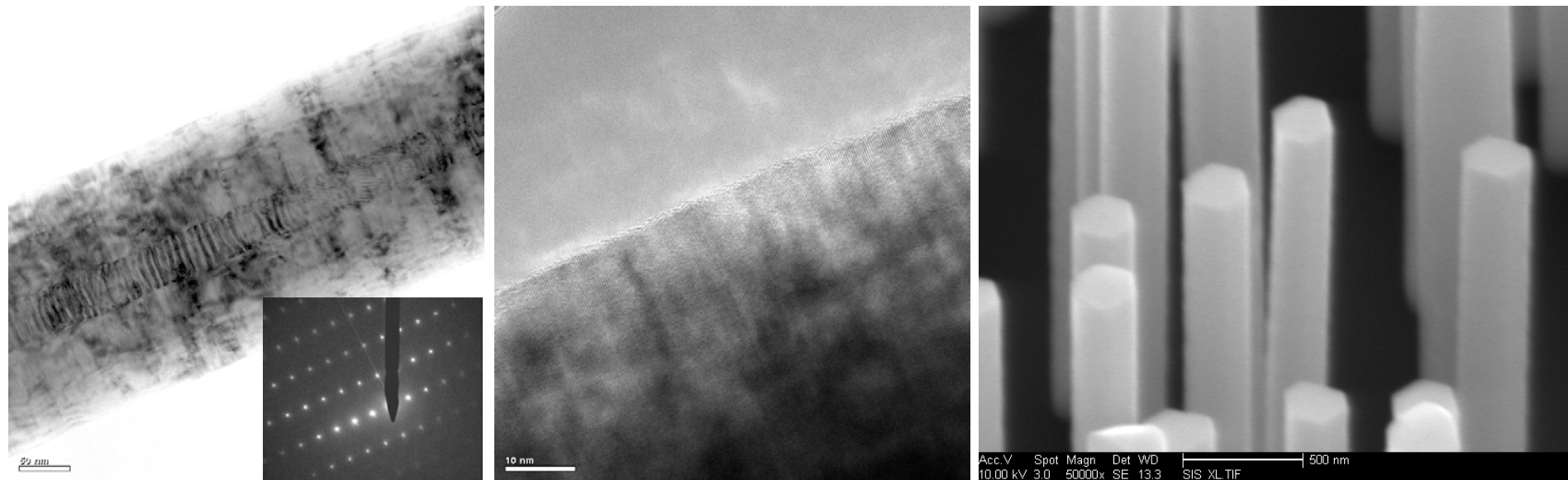
[B. J. Soller, H. R. Stuart, D. G. Hall, *Opt. Lett.* **26**, 1421 (2001).]

- High refractive index contrast allows ~60-90% coupling efficiency of scattered light into guided modes over broad range of wavelength
- Wafer thinning/bonding and related materials integration techniques enable quantum-well solar cell structures with optimum waveguiding and coupling
- Preliminary simulations indicate that with minimal optimization, >1.25x improvement in efficiency compared to same cell without scattering (but with antireflection coating) is attainable



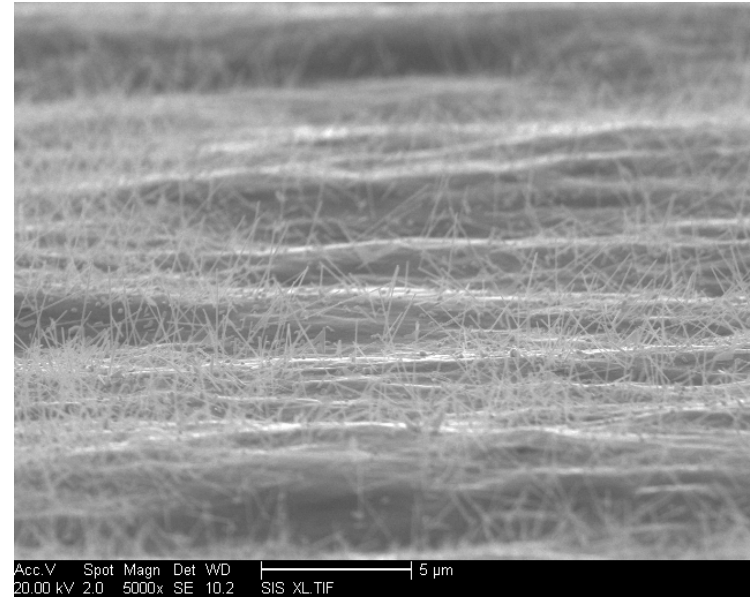
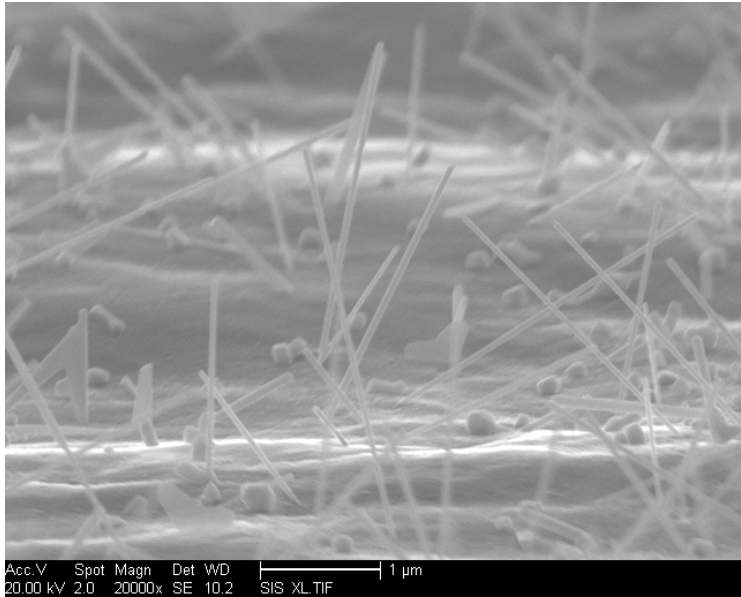
- n-InAs nanowires successfully grown on Si (111) substrates
- InAs nanowires on Si exhibit photovoltaic device behavior, but with low power conversion efficiency ($\sim 1\text{-}2.5\%$)
- InAs nanowires can eventually serve as core of high-efficiency core-shell nanowire heterostructure photovoltaic device

Results – nanowire heterostructure growth



- Growth of uniform core/multi-shell heterostructures (InAs/InGaAs/GaAs/InGaP) successfully demonstrated
- Core/multi-shell heterostructures could serve as basic element of high-efficiency nanowire photovoltaic devices
- Interestingly, nanowires are (111) zincblende rather than wurtzite, as is typical

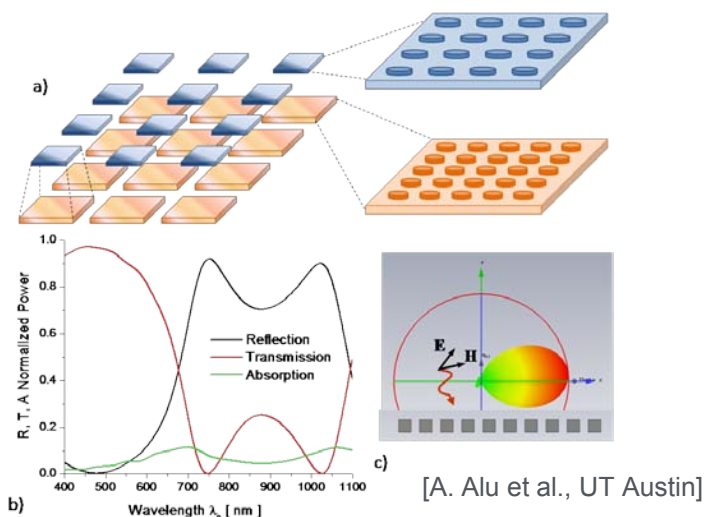
Results – nanowire growth on low-cost metal foil substrate



InAs nanowires grown on Al foil

- InAs nanowires have been successfully grown by MOCVD directly on low-cost metal foil substrates, e.g., Au or Cu foils
- High-quality nanowire growth on low-cost substrates could help enable low-cost, high-efficiency nanowire-based photovoltaic devices

- Project is on budget
 - Total DOE funding of \$604,000 to date + 20% cost share
 - In process of transitioning portion of funding from UCSD to UT Austin
- Potential area for expansion: integration of nanostructure scattering and photon management concepts into optical slab concentrator structures for new high-efficiency photovoltaic device concept:



- Optical metamaterials enable wavelength-dependent transmission and scattering of incident light
- Metamaterials integrated with optical slab concentrator could enable mm-scale photon management techniques to be exploited in high-efficiency multijunction solar cell concept

- Project plans for FY2010 and FY2011:
 - Fabrication and demonstration of ultrathin quantum-well solar cell device with optimized optical coupling to device waveguide modes
 - Continued engineering of quantum-confined structures for improved optical absorption
 - Nanowire growth and device development on low-cost substrates and with heterostructures for improved power conversion efficiency
- Upcoming key milestones:
 - 7/1/10, 1/31/11: fabrication and characterization of quantum-well solar cell device incorporating substrate removal process, antireflection coating, and nanostructured scattering elements
 - 7/1/10, 1/31/11: demonstration of improved power conversion efficiency in nanowire photovoltaic devices

- New solar cell concepts offering high power conversion efficiency over broad range of illumination conditions likely to be needed for applications such as concentrating photovoltaics
- Quantum-well solar cells and related concepts offer theoretically predicted efficiencies of ~45% to >60% over broad range of illumination conditions
 - Plasmonics and nanoparticle scattering effects can facilitate simultaneously high efficiency in both optical absorption and photogenerated carrier collection
 - Nanowires offer alternate geometry for these concepts as well as potential for direct integration on low-cost substrates
- Key basic elements have been successfully demonstrated:
 - Photocurrent response over extended wavelength range due to quantum-well absorption
 - Plasmonic and nanoparticle scattering for improved long-wavelength optical absorption
 - Engineering of internal quantum well structure (potential steps within quantum well, dot-in-well structures) used to further improve optical absorption
 - Numerical simulations and designs developed for ultrathin, high-efficiency devices
 - III-V nanowire growth on Si substrates and photovoltaic device operation achieved
 - Nanowire core-shell heterostructure growth and growth on low-cost metal foil substrates achieved
- Program on track for demonstration of high-efficiency devices based on these concepts
- Potential for program expansion to exploit photon management concepts in more complex high-efficiency device geometries